



CLP30-200B1

Application Specific Discretes
A.S.D™

OVERVOLTAGE & OVERCURRENT PROTECTION FOR TELECOM LINE

MAIN APPLICATIONS

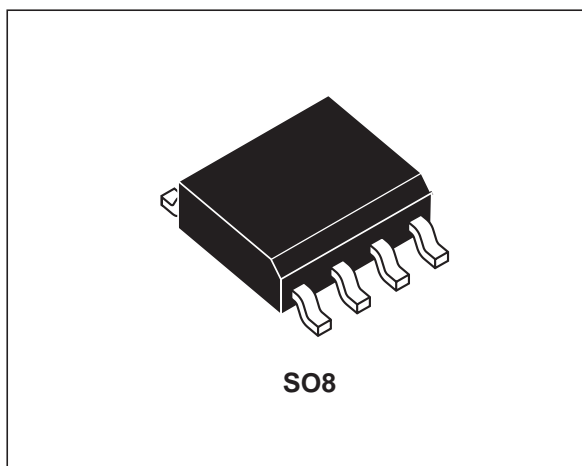
Any telecom equipment submitted to transient overvoltages and lightning strikes such as :

- Analog and ISDN line cards
- PABX

DESCRIPTION

The CLP30-200B1 is designed to protect telecommunication equipment. It provides both a transient overvoltage protection and an overcurrent protection.

The external components (balanced resistors, ring relays contact, ...) needed by the CLP30-200B1 protection concept require very low power rating. This results in a very cost effective protection solution.



SO8

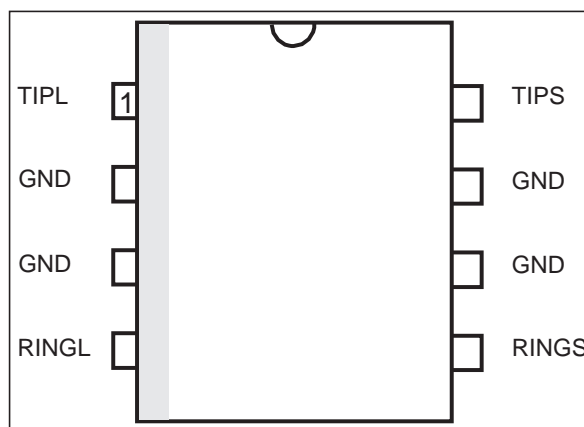
FEATURES

- Dual bidirectional protection device.
- High peak pulse current :
 $I_{PP} = 40A$ (5/310 μs SURGE)
 $I_{PP} = 30A$ (10/1000 μs SURGE)
- Max. voltage at switching-on : 290V
- Min. current at switching-off : 150mA

BENEFITS

- Voltage and current controlled suppression.
- Surface Mounting with SO8 package.
- Very low power rating of external components on line card : balanced resistors, ring relay, low voltage SLIC protection.

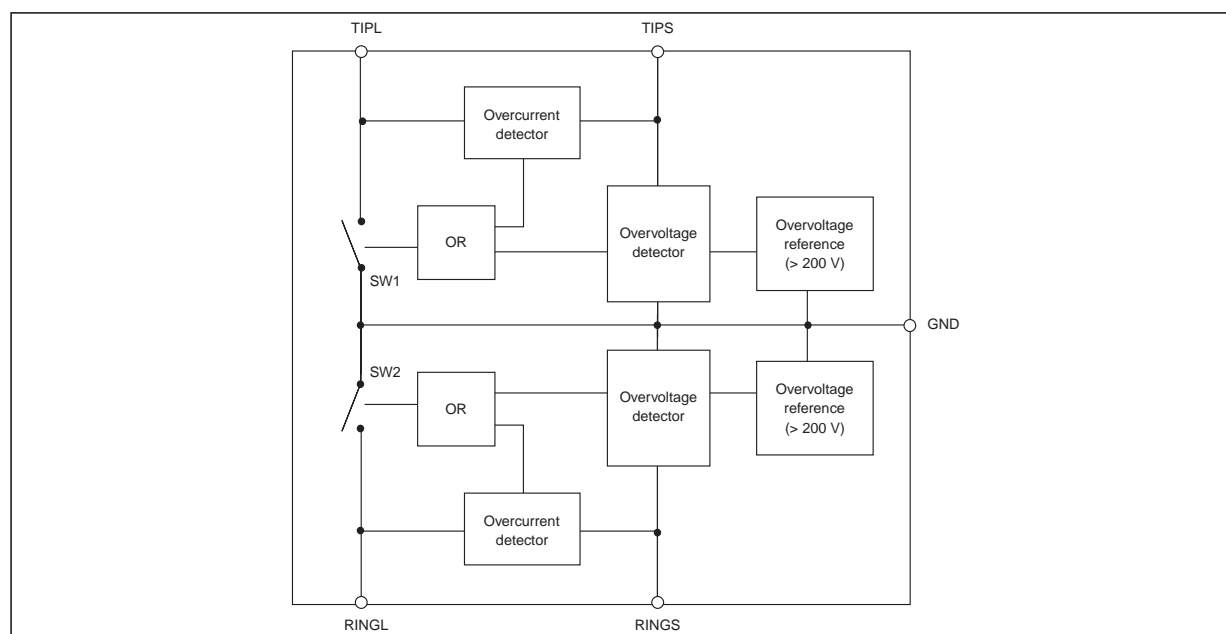
SCHEMATIC DIAGRAM (Top view)



CLP30-200B1

Standard	Peak surge voltage (V)	Voltage waveform	Required peak current (A)	Current waveform	Minimum serial resistor to meet standard (Ω)
Bellcore TR-NWT-1089 First level	2500 1000	2/10 μ s 10/100 μ s	500 100	2/10 μ s 10/1000 μ s	20 25
Bellcore TR-NWT-1089 Second level	5000	2/10 μ s	500	2/10 μ s	40
ITU-T-K20 / K21	4000 1000	10/700 μ s	100 25	5/310 μ s	50 0
ITU-T-K20 (IEC61000-4-2)	6000 8000	1/60 ns	ESD contact discharge ESD air discharge		0 0
VDE0433	4000 2000	10/700 μ s	100 50	5/310 μ s	50 5
VDE0878	4000 2000	1.2/50 μ s	100 50	1/20 μ s	22 0
IEC61000-4-5	4000 2000 4000	10/700 μ s 1.2/50 μ s 1.2/50 μ s	100 50 100	5/310 μ s 8/20 μ s 8/20 μ s	50 0 22
FCC Part 68, lightning surge type A	1500 800	10/160 μ s 10/560 μ s	200 100	10/160 μ s 10/560 μ s	17.5 12
FCC Part 68, lightning surge type B	1000	9/720 μ s	25	5/320 μ s	0

BLOCK DIAGRAM



Pin	Symbol	Description
1	TIPL	TIP (Line side)
2 / 3 / 6 / 7	GND	Ground
4	RINGL	RING (Line side)
5	RINGS	RING (SLIC side)
8	TIPS	TIP (SLIC side)

APPLICATION NOTE

1. INTRODUCTION

The aim of this section is to show the behavior of our new telecom line protection device.

Fig.1 : Subscriber line protection topology

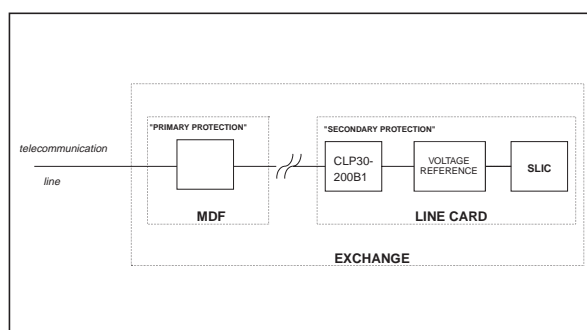


Figure 1 is a simplified block diagram of a subscriber line protection that is mainly used so far.

This shows two different things :

- A “primary protection” located on the Main Distribution Frame (MDF) eliminates coarsely the high energy environmental disturbances (lightning transients and AC power mains disturbances) for which the ITU-T-K20 requires a 4kV 10/700 μ s test. This can be assumed either by gas-tubes or silicon protection such as the TLPxxM.
- A “secondary protection” located on the line card eliminates finely the remaining transients that have not been totally suppressed by the first stage. The ITU-T-K20 requires a 1 kV 10/700 μ s test. At this stage, the protection is managed by the CLP30-200B1.

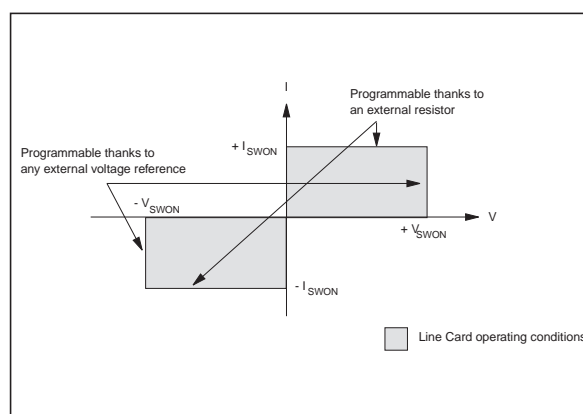
2. STMicroelectronics CLP30-200B1 CONCEPT

2.1 Evolution of the SLIC protection

Over the years, the performances of the SLICs considerably increased and therefore the need of the protection has also evolved.

The CLP30-200B1 is especially designed for the protection of this new generation of SLIC. For this, it is based on both overvoltage and overcurrent protection modes.

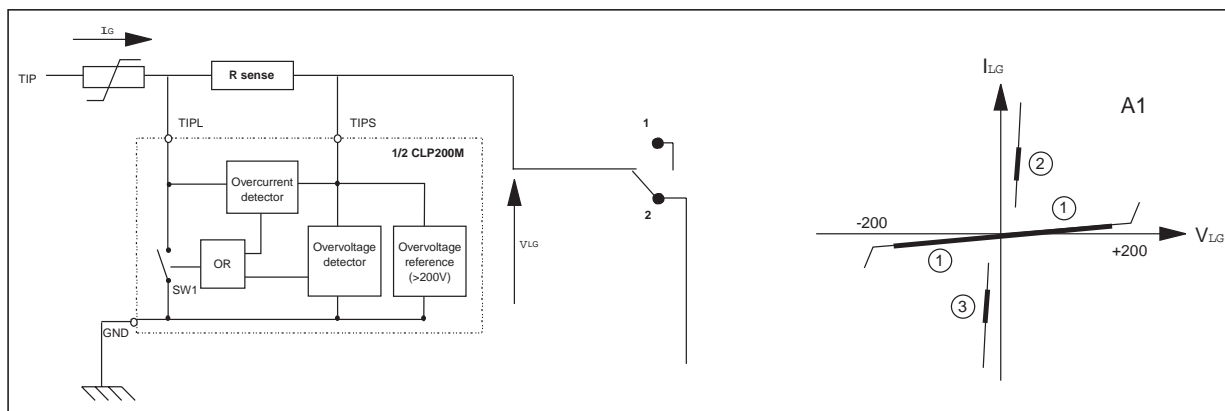
Fig.2 : Line card protection



The **figure 2** summarises the performance of the CLP30-200B1 which basically holds the SLIC inside its correct voltage and current values.

2.3 Ringing mode

Fig.4 : Switching by voltage during ringing mode.



In ringing mode (Ring relay in position 2), the only protection device involved is the CLP30-200B1.

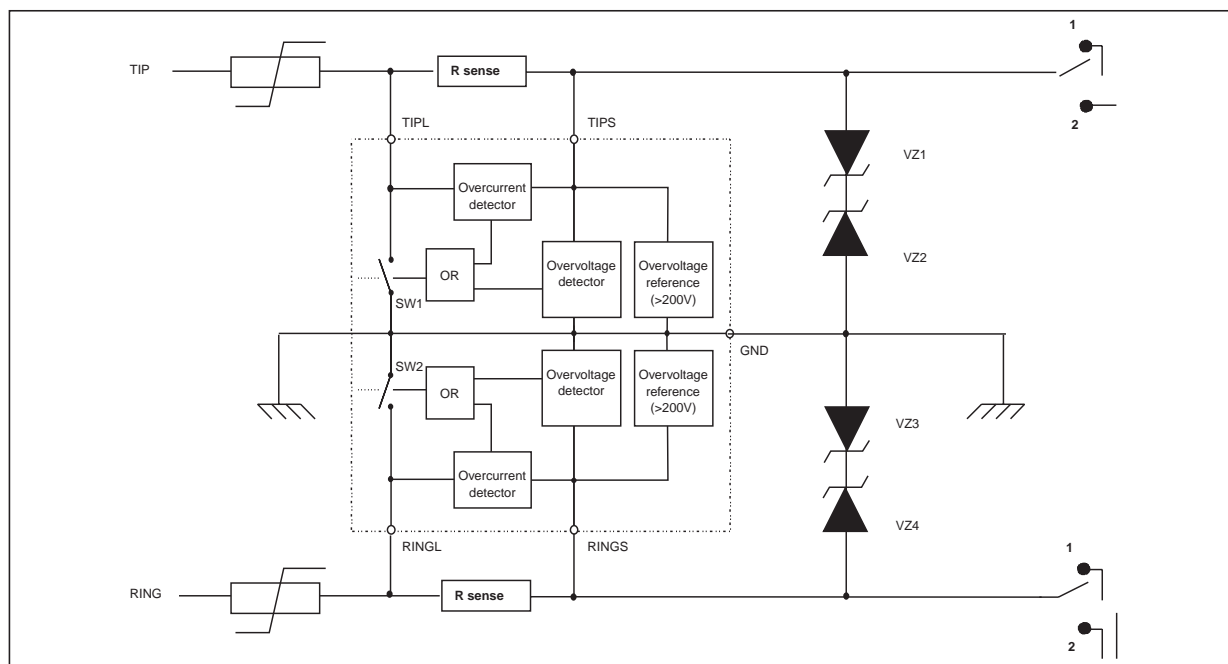
In normal conditions, the CLP30-200B1 operates in region 1 of **A1** curve, and is idle.

If an overvoltage occurring between TIP (or RING) and GND reaches the internal overvoltage reference (+/- 200V), the CLP30-200B1 acts and the line is short-circuited to GND. At this time the operating point moves to region 2 for positive surges (region 3 for negative surges). Once the surge current disappears, the device returns to its initial state (region 1).

For surges occurring between TIP and RING, the CLP30-200B1 acts in the same way. This means that the CLP30-200B1 ensures a tripolar protection.

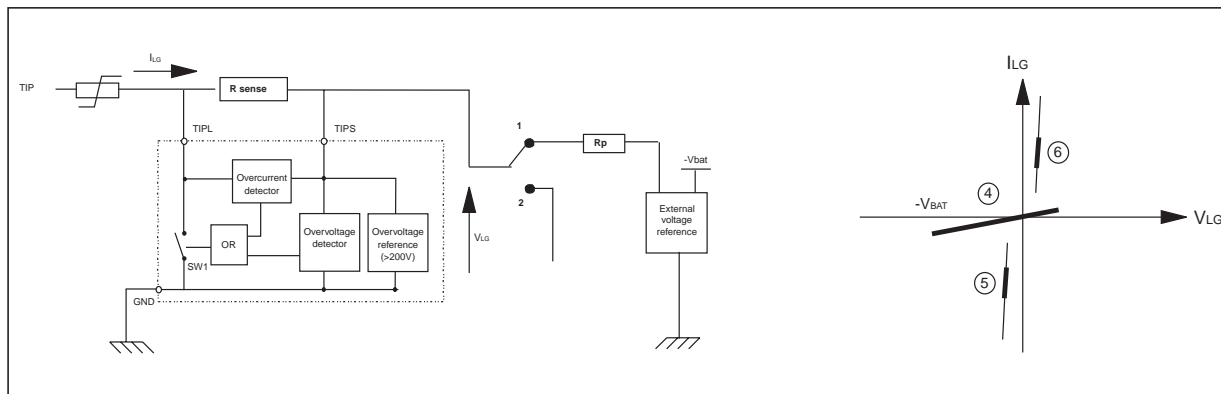
When used alone, the CLP30-200B1 acts at the internal overvoltage reference level (+/- 200 V). Furthermore, it is possible to adjust this threshold level to a lower voltage by using up to 4 fixed external voltage reference (V_{Z1} to V_{Z4}) (see fig.5).

Fig.5 : Methode to adjust the reference voltage.



2.4 Speech mode

Fig.6 : Switching by current during speech mode.



In speech mode (Ring relay in position 1), the protection is provided by the combination of both CLP30-200B1 and the external voltage reference device (for example LCP1511D).

In normal conditions, the working point of this circuit is located in region 4 of **A2** curve : the CLP30-200B1 is idle.

When a surge occurs on the line, the external voltage reference device clamps at GND or $-V_{bat}$ respectively for positive and negative surges. This generates a current which is detected by R_{sense} and causes the protection to act : the line is short-circuited to GND. The operating point moves to region 6 for positive surges or region 5 for negative surges.

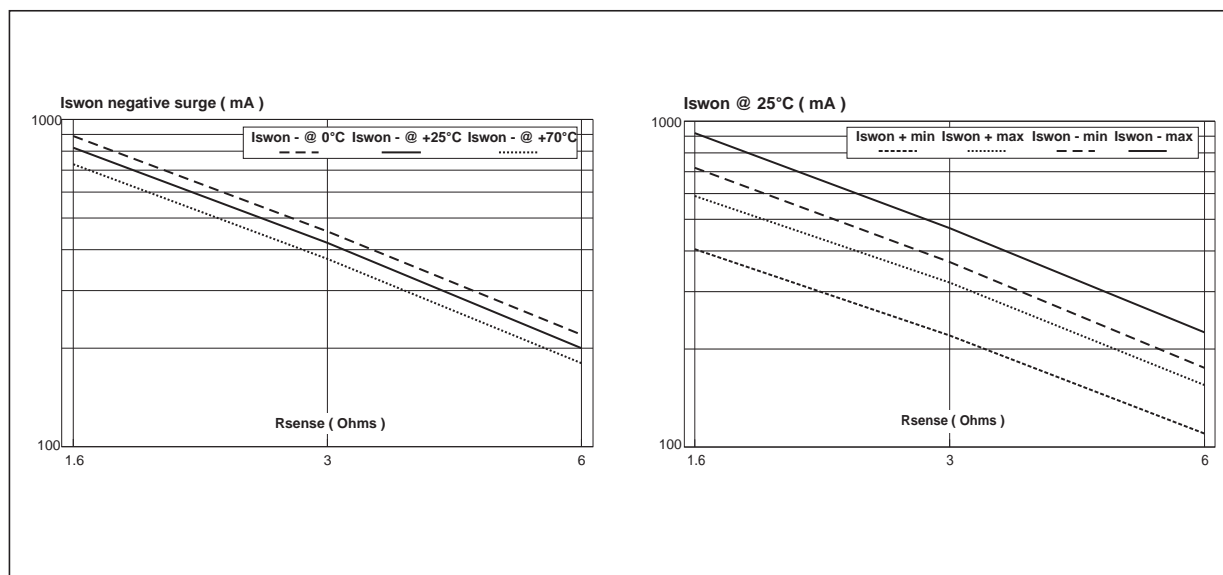
Once the surge current falls below the switching-off current I_{SWOFF} , the CLP30-200B1 returns to its initial state (region 4).

Furthermore, the CLP30-200B1 switches when an overvoltage, either positive or negative, occurs either :

- simultaneously on both TIP and RING lines versus GND.
- between TIP and RING.
- on TIP (or RING) versus GND.

The choice of the switching-on current is function of the R_{SENSE} resistors.

Fig . 7a and 7b : Switching-on current versus R_{SENSE}



This current (typically above 150 mA) should not activate the protection device CLP30-200B1.

Therefore the level of activation is to be chosen just below this limit (typically 200mA). This level is adjusted through R_{SENSE} .

Figures 7a and 7b enable the designers to choose the right R_{SENSE} value.

Example: The choice of $R_{\text{SENSE}} = 3 \Omega$ ensures a negative triggering of -280 mA min and -380mA max. In this case, the positive triggering will be 220mA min and 320mA max.

Thanks to the CLP30-200B1 topology, the surge current in the line is reduced after it.

Because the remaining surge energy is low, the power ratings of R_P , the relay contacts and the external voltage reference device may be kept low. This results in a significant cost reduction for the whole system.

CLP30-200B1

ABSOLUTE MAXIMUM RATINGS ($R_{\text{SENSE}} = 3\ \Omega$, $T_{\text{amb}} = 25^{\circ}\text{C}$)

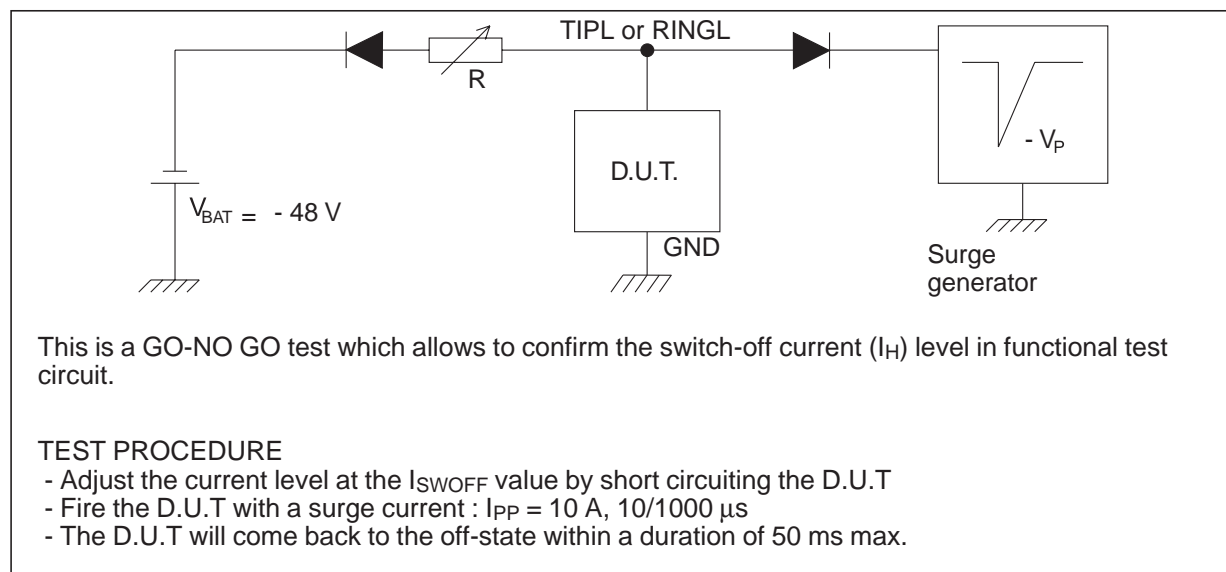
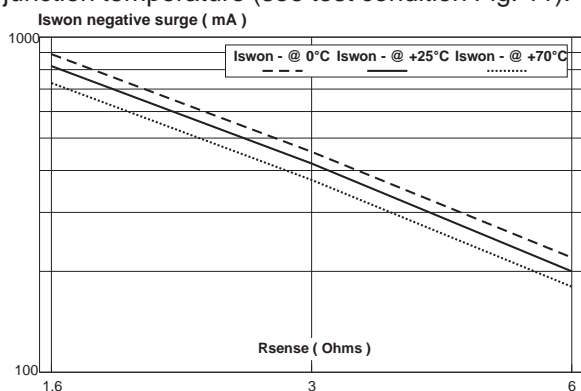
Symbol	Parameter	Value	Unit
I_{PP}	Line to GND peak pulse current 10/1000 μs (open circuit voltage wave shape 10/1000 μs) 5/310 μs (open circuit voltage wave shape 10/700 μs)	30 45	A
I_{TSM}	Non repetitive surge peak on-state current $F = 50\ \text{Hz}$	$t_p = 10\ \text{ms}$ $t_p = 200\ \text{ms}$ $t_p = 1\ \text{s}$	8.5 4.5 3.5 A
T_{stg} T_j	Storage temperature range Maximum junction temperature	-40 to +150 150	$^{\circ}\text{C}$
T_L	Lead temperature for soldering during 10 s.	260	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($R_{\text{SENSE}} = 3\ \Omega$, and $T_{\text{amb}} = 25\ ^{\circ}\text{C}$)

Symbol	Parameter	Test conditions	Min	Max	Unit
I_{LGL}	Line to GND leakage current	$V_{\text{LG}} = 200\ \text{V}$ Measured between TIP (or RING) and GND		10	μA
V_{LG}	Line to GND operating voltage		200		V
V_{SWON}	Line to GND voltage at SW1 or SW2 switching-on	Measured at 50 Hz between TIPL (or RINGL) and GND, one cycle		290	V
I_{SWOFF}	Line to GND negative current at SW1 or SW2 switching-off	Refer to test circuit fig 9	150		mA
I_{SWON}	Line current at SW1 or SW2 switching-on	Positive surge Negative surge	220 370	320 470	mA
C	Line to GND capacitance	$V_{\text{LG}} = 0\ \text{V}$ $V_{\text{OSC}} = 200\ \text{mV}_{\text{RMS}}$ $F = 1\ \text{MHz}$		100	pF

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{\text{th(j-a)}}$	Junction to ambient	170	$^{\circ}\text{C/W}$

Fig.8 : TEST CIRCUIT FOR I_{SWOFF} PARAMETER : GO - NO GO TEST**Fig. 9 : Typical variation of switching-on current (positive or negative) versus R_{SENSE} resistor and junction temperature (see test condition Fig. 11).****Fig. 11 : I_{swon} MEASUREMENT**

- $I_{swon} = I_1$ when the CLP30-200B1 switches on (I_1 is progressively increased using R)
- Both TIP and RING sides of the CLP30-200B1 are checked
- $R_L = 10 \Omega$.

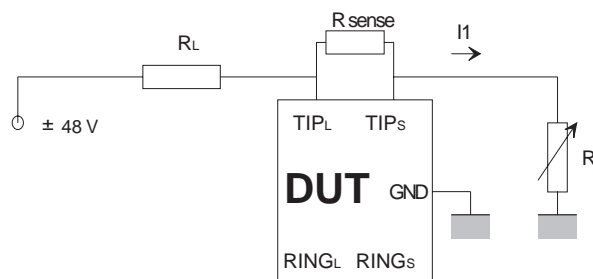
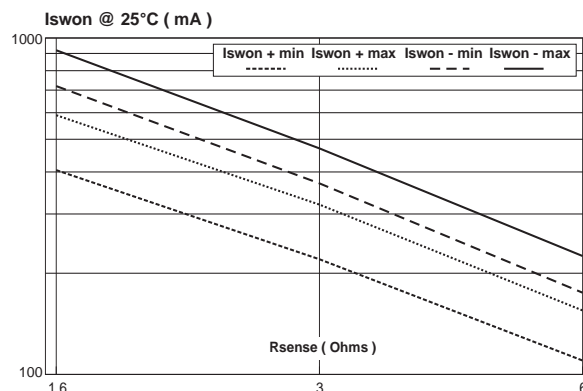
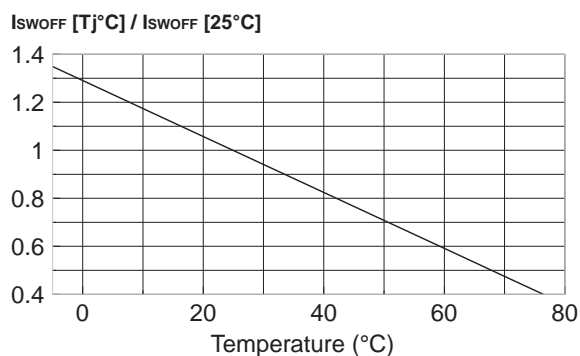
**Fig. 10 : Variation of switching-on current versus R_{SENSE} at 25 °C.****fig. 12 : Relative variation of switching-off current versus junction temperature (for R_{SENSE} between 3 and 10Ω).**

Fig. 13 : Relative variation of switching-off current versus R_{SENSE} (between 3 and 10 Ω).

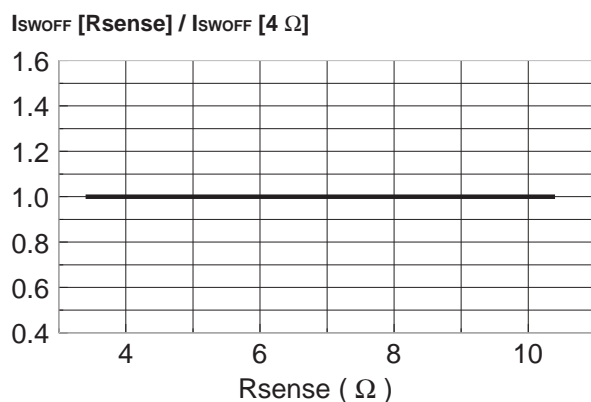


Fig. 15 : Relative variation of internal reference voltage versus junction temperature ($I_{LG} = 1\text{mA}$).

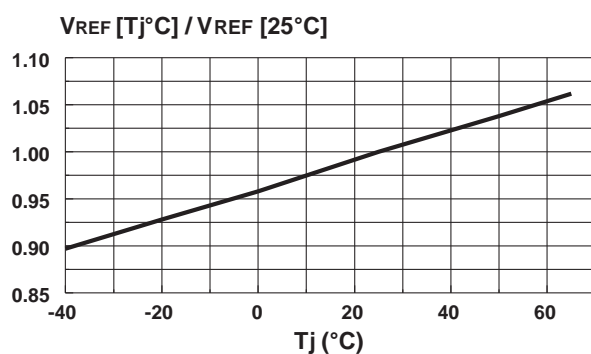


Fig. 17 : Surge peak current versus overload duration (maximum values).

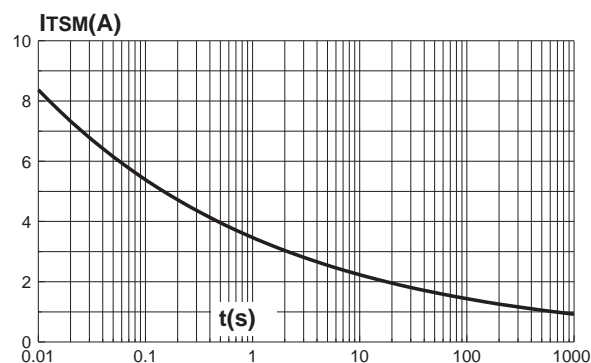


Fig. 14 : Relative variation of switching-on voltage versus dV/dt with an external resistor of 3 Ω .

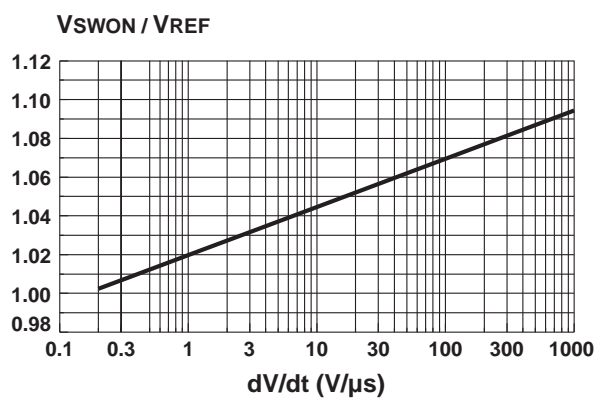
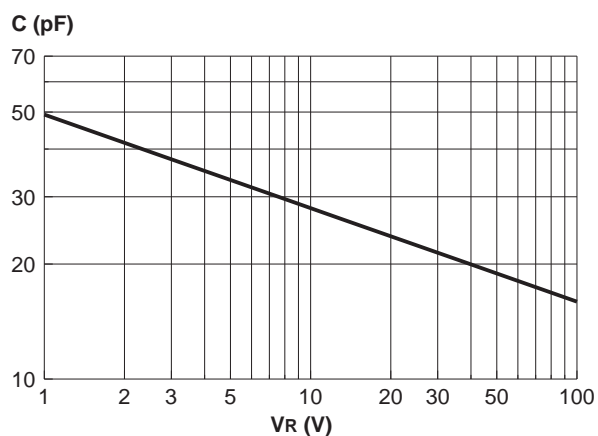


Fig. 16 : Capacitance (TIP/GND) versus applied voltage (typical values).



PACKAGE MECHANICAL DATA
SO8 plastic

REF.	DIMENSIONS					
	Millimetres			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
C	0.25	0.50	0.50	0.010		0.020
c1	45° (typ)					
D	4.8		5.0	0.189		0.197
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.15		0.157
L	0.4		1.27	0.016		0.050
M			0.6			0.024
S	8° (max)					

MARKING

Ordering code	Marking	Package	Weight	Base qty	Delivery mode
CLP30-200B1	CLP30	SO-8	0.08g	100	Tube
CLP30-200B1RL	CLP30	SO-8	0.08g	2500	Tape & Reel

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